

Amendments to the Specification

Replace the title with the following amended title:

~~Nitride Based Semiconductor Light-Emitting Device and Method of Manufacturing the Same~~

Replace the paragraph at page 21, lines 13-22, with the following amended paragraph:

As shown in Fig. 9, this light-emitting device of the embodiment includes Si doped n-type GaN contact layer 12 as a ~~first~~ first conductive type nitride based semiconductor layer and n-type AlGaN clad layer 13 which are, by turn, formed on the (0001) C plane of sapphire substrate 11. The multi-layer structure of InGa/GaN of MQW active layer 14 is formed on n-type AlGaN clad layer 13 as an active layer of a nitride based semiconductor layer with a p-n junction. Further, Mg doped p-type AlGaN clad layer 15 and p-type GaN contact layer 16 are, by turn, formed as second conductive type nitride based semiconductor layers.

Replace the abstract with the following amended abstract

~~Nitride based semiconductor light-emitting devices are provided with a sufficiently low contact resistance p-type electrode and a method of manufacturing the same are disclosed. One such method of manufacturing nitride based semiconductor light-emitting devices includes steps of growing island like AlGaN films 17 on p-type nitride based semiconductor layer 16, etching a surface of p-type nitride based semiconductor layer 16 to make uneven portions 18 on its surface by using island like AlGaN films 17 as a photomask, and forming of a p-type ohmic electrode on an electrode forming region of the uneven portion 18. The nitride based semiconductor light-emitting devices include a p-type GaN contact layer, protrusions with fine recesses (uneven portions) formed on a surface of the p-type GaN contact layer, and a p-type electrode formed on the uneven portions.~~